Toshio Kamiya

List of Publications by Year
in descending order

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243 papers	31,367 citations	7568 77 h-index	4228 174 g-index
249 all docs	249 docs citations	249 times ranked	14831 citing authors

#	Article	IF	Citations
1	Room-temperature fabrication of transparent flexible thin-film transistors using amorphous oxide semiconductors. Nature, 2004, 432, 488-492.	27.8	6,503
2	Thin-Film Transistor Fabricated in Single-Crystalline Transparent Oxide Semiconductor. Science, 2003, 300, 1269-1272.	12.6	1,709
3	Present status of amorphous Inâ€“Gaâ€“Znâ€“O thin-film transistors. Science and Technology of Advanced Materials, 2010, 11, 044305.	6.1	1,559
4	Iron-Based Layered Superconductor:Â LaOFeP. Journal of the American Chemical Society, 2006, 128, 10012-10013.	13.7	1,207
5	High-mobility thin-film transistor with amorphous InGaZnO4 channel fabricated by room temperature rf-magnetron sputtering. Applied Physics Letters, 2006, 89, 112123.	3.3	1,048
6	Material characteristics and applications of transparent amorphous oxide semiconductors. NPG Asia Materials, 2010, 2, 15-22.	7.9	852
7	High-Density Electron Anions in a Nanoporous Single Crystal: [Ca24Al28O64]4+(4e-). Science, 2003, 301, 626-629.	12.6	744
8	Amorphous Oxide Semiconductors for High-Performance Flexible Thin-Film Transistors. Japanese Journal of Applied Physics, 2006, 45, 4303-4308.	1.5	659
9	p -channel thin-film transistor using p-type oxide semiconductor, SnO. Applied Physics Letters, 2008, 93, .	3.3	577
10	Origins of High Mobility and Low Operation Voltage of Amorphous Oxide TFTs: Electronic Structure, Electron Transport, Defects and Doping. Journal of Display Technology, 2009, 5, 273-288.	1.2	464
11	Light-induced conversion of an insulating refractory oxide into a persistent electronic conductor. Nature, 2002, 419, 462-465.	27.8	431
12	Carrier transport and electronic structure in amorphous oxide semiconductor, a-InGaZnO4. Thin Solid Films, 2005, 486, 38-41.	1.8	423
13	Fabrication and photoresponse of a pn-heterojunction diode composed of transparent oxide semiconductors, p-NiO and n-ZnO. Applied Physics Letters, 2003, 83, 1029-1031.	3.3	329
14	Origins of threshold voltage shifts in room-temperature deposited and annealed a-Inâ€“Gaâ€“Znâ€“O thin-film transistors. Applied Physics Letters, 2009, 95, .	3.3	324
15	Modeling of amorphous InGaZnO4 thin film transistors and their subgap density of states. Applied Physics Letters, 2008, 92, .	3.3	318
16	Subgap states in transparent amorphous oxide semiconductor, Inâ€“Gaâ€“Znâ€“O, observed by bulk sensitive x-ray photoelectron spectroscopy. Applied Physics Letters, 2008, 92, .	3.3	298
17	Trap densities in amorphous-InGaZnO4 thin-film transistors. Applied Physics Letters, 2008, 92, .	3.3	290
18	Defect passivation and homogenization of amorphous oxide thin-film transistor by wet O2 annealing. Applied Physics Letters, 2008, 93, .	3.3	276

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19	Local coordination structure and electronic structure of the large electron mobility amorphous oxide semiconductor In-Ga-Zn-O: Experiment andab initiocalculations. Physical Review B, 2007, 75, .	3.2	275
20	Nickel-Based Oxyphosphide Superconductor with a Layered Crystal Structure, LaNiOP. Inorganic Chemistry, 2007, 46, 7719-7721.	4.0	268
21	Crystal Structures, Optoelectronic Properties, and Electronic Structures of Layered Oxychalcogenides MCuOCh (M = Bi, La; Ch = S, Se, Te): Effects of Electronic Configurations of M³⁺ Ions. Chemistry of Materials, 2008, 20, 326-334.	6.7	258
22	Carrier transport in transparent oxide semiconductor with intrinsic structural randomness probed using single-crystalline InGaO3(ZnO)5 films. Applied Physics Letters, 2004, 85, 1993-1995.	3.3	247
23	Advantageous grain boundaries in iron pnictide superconductors. Nature Communications, 2011, 2, 409.	12.8	246
24	Ambipolar Oxide Thinâ€Film Transistor. Advanced Materials, 2011, 23, 3431-3434.	21.0	236
25	Epitaxial growth of high mobility Cu2O thin films and application to p-channel thin film transistor. Applied Physics Letters, 2008, 93, .	3.3	222
26	Combinatorial approach to thin-film transistors using multicomponent semiconductor channels: An application to amorphous oxide semiconductors in Inâ€“Gaâ€“Znâ€“O system. Applied Physics Letters, 2007, 90, 242114.	3.3	219
27	Electronic Structures Above Mobility Edges in Crystalline and Amorphous In-Ga-Zn-O: Percolation Conduction Examined by Analytical Model. Journal of Display Technology, 2009, 5, 462-467.	1.2	219
28	Electronic structure of oxygen deficient amorphous oxide semiconductor aâ€InGaZnO_{4â€“x}: Optical analyses and firstâ€principle calculations. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3098-3100.	0.8	214
29	Tin monoxide as an sâ€orbitalâ€based pâ€type oxide semiconductor: Electronic structures and TFT application. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2187-2191.	1.8	213
30	Metallic State in a Limeâ^'Alumina Compound with Nanoporous Structure. Nano Letters, 2007, 7, 1138-1143.	9.1	208
31	Electronic structure of the amorphous oxide semiconductor aâ€InGaZnO_{4â€“x}: Taucâ€“Lorentz optical model and origins of subgap states. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 860-867.	1.8	207
32	UV-detector based on pn-heterojunction diode composed of transparent oxide semiconductors, p-NiO/n-ZnO. Thin Solid Films, 2003, 445, 317-321.	1.8	206
33	Effects of excess oxygen on operation characteristics of amorphous In-Ga-Zn-O thin-film transistors. Applied Physics Letters, 2011, 99, .	3.3	203
34	Specific contact resistances between amorphous oxide semiconductor Inâ€“Gaâ€“Znâ€“O and metallic electrodes. Thin Solid Films, 2008, 516, 5899-5902.	1.8	191
35	Effects of Diffusion of Hydrogen and Oxygen on Electrical Properties of Amorphous Oxide Semiconductor, In-Ga-Zn-O. ECS Journal of Solid State Science and Technology, 2013, 2, P5-P8.	1.8	191
36	Sputtering formation of p-type SnO thin-film transistors on glass toward oxide complimentary circuits. Applied Physics Letters, 2010, 97, .	3.3	189

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37	Growth, structure and carrier transport properties of Ga2O3 epitaxial film examined for transparent field-effect transistor. Thin Solid Films, 2006, 496, 37-41.	1.8	173
38	Amorphous Inâ€“Gaâ€“Znâ€“O coplanar homojunction thin-film transistor. Applied Physics Letters, 2009, 94, 133502.	3.3	168
39	Degenerate p-type conductivity in wide-gap LaCuOS1âˆ’xSex (x=0â€“1) epitaxial films. Applied Physics Letters, 2003, 82, 1048-1050.	3.3	166
40	Amorphous oxide channel TFTs. Thin Solid Films, 2008, 516, 1516-1522.	1.8	166
41	Factors controlling electron transport properties in transparent amorphous oxide semiconductors. Journal of Non-Crystalline Solids, 2008, 354, 2796-2800.	3.1	162
42	Highly stable amorphous In-Ga-Zn-O thin-film transistors produced by eliminating deep subgap defects. Applied Physics Letters, 2011, 99, .	3.3	156
43	Depth analysis of subgap electronic states in amorphous oxide semiconductor, a-In-Ga-Zn-O, studied by hard x-ray photoelectron spectroscopy. Journal of Applied Physics, 2011, 109, 073726.	2.5	151
44	Two-Dimensional Transition-Metal Electride Y₂C. Chemistry of Materials, 2014, 26, 6638-6643.	6.7	151
45	Proton Conduction in In[sup 3+]-Doped SnP[sub 2]O[sub 7] at Intermediate Temperatures. Journal of the Electrochemical Society, 2006, 153, A1604.	2.9	149
46	Subgap states, doping and defect formation energies in amorphous oxide semiconductor aâ€InGaZnO₄ studied by density functional theory. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1698-1703.	1.8	149
47	Bipolar Conduction in SnO Thin Films. Electrochemical and Solid-State Letters, 2011, 14, H13.	2.2	148
48	Origin of definite Hall voltage and positive slope in mobility-donor density relation in disordered oxide semiconductors. Applied Physics Letters, 2010, 96, .	3.3	139
49	Itinerant ferromagnetism in the layered crystals <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>LaCoO</mml:mtext><mml:mi>X</mml:mi><mml:mspace width="0.3em" /><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mi>X</mml:mi><mml:mo>=</mml:mo><mml:mtext>P</mml:mtext><mml:mo	3.2	138
50	Physical Review B, 2008, 77, . Field-induced current modulation in epitaxial film of deep-ultraviolet transparent oxide semiconductor Ga2O3. Applied Physics Letters, 2006, 88, 092106.	3.3	137
51	Oligomerization of adenosine A2A and dopamine D2 receptors in living cells. Biochemical and Biophysical Research Communications, 2003, 306, 544-549.	2.1	133
52	Frontier of transparent oxide semiconductors. Solid-State Electronics, 2003, 47, 2261-2267.	1.4	129
53	Circuits using uniform TFTs based on amorphous Inâ€Gaâ€Znâ€O. Journal of the Society for Information Display, 2007, 15, 915-921.	2.1	121
54	Fabrication and characterization of heteroepitaxial p-n junction diode composed of wide-gap oxide semiconductors p-ZnRh2O4/n-ZnO. Applied Physics Letters, 2003, 82, 823-825.	3.3	119

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55	Nickel-based phosphide superconductor with infinite-layer structure, BaNi2P2. Solid State Communications, 2008, 147, 111-113.	1.9	118
56	Hydrogen passivation of electron trap in amorphous In-Ga-Zn-O thin-film transistors. Applied Physics Letters, 2013, 103, .	3.3	112
57	Fast Thin-Film Transistor Circuits Based on Amorphous Oxide Semiconductor. IEEE Electron Device Letters, 2007, 28, 273-275.	3.9	110
58	Biaxially textured cobalt-doped BaFe2As2 films with high critical current density over 1â€‚MA/cm2 on MgO-buffered metal-tape flexible substrates. Applied Physics Letters, 2011, 98, 242510.	3.3	110
59	Superconductivity in Epitaxial Thin Films of Co-Doped SrFe2As2with Bilayered FeAs Structures and their Magnetic Anisotropy. Applied Physics Express, 2008, 1, 101702.	2.4	103
60	Nickel-based layered superconductor, LaNiOAs. Journal of Solid State Chemistry, 2008, 181, 2117-2120.	2.9	99
61	Femtosecond-laser-encoded distributed-feedback color center laser in lithium fluoride single crystals. Applied Physics Letters, 2004, 84, 311-313.	3.3	97
62	Single-atomic-layered quantum wells built in wide-gap semiconductorsLnCuOCh(Ln=lanthanide,Ch=chalcogen). Physical Review B, 2004, 69, .	3.2	97
63	Optical and electrical properties of amorphous zinc tin oxide thin films examined for thin film transistor application. Journal of Vacuum Science & Technology B, 2008, 26, 495-501.	1.3	96
64	Intermediate-Temperature Proton Conduction in Al[sup 3+]-Doped SnP[sub 2]O[sub 7]. Journal of the Electrochemical Society, 2007, 154, B1265.	2.9	95
65	Heavy hole doping of epitaxial thin films of a wide gap p-type semiconductor, LaCuOSe, and analysis of the effective mass. Applied Physics Letters, 2007, 91, .	3.3	91
66	Heteroepitaxial growth and optoelectronic properties of layered iron oxyarsenide, LaFeAsO. Applied Physics Letters, 2008, 93, 162504.	3.3	91
67	Three-dimensionally stacked flexible integrated circuit: Amorphous oxide/polymer hybrid complementary inverter using n-type a-Inâ€“Gaâ€“Znâ€“O and p-type poly-(9,9-dioctylfluorene-co-bithiophene) thin-film transistors. Applied Physics Letters, 2010, 96, .	3.3	91
68	Structural relaxation in amorphous oxide semiconductor, a-In-Ga-Zn-O. Journal of Applied Physics, 2012, 111, .	2.5	90
69	Diffusion-Limited a-IGZO/Pt Schottky Junction Fabricated at 200 $^{circ}hbox{C}$ on a Flexible Substrate. IEEE Electron Device Letters, 2011, 32, 1695-1697.	3.9	89
70	A germanate transparent conductive oxide. Nature Communications, 2011, 2, 470.	12.8	88
71	Wide-gap layered oxychalcogenide semiconductors: Materials, electronic structures and optoelectronic properties. Thin Solid Films, 2006, 496, 8-15.	1.8	86
72	Electron field emission from TiO2 nanotube arrays synthesized by hydrothermal reaction. Applied Physics Letters, 2006, 89, 043114.	3.3	84

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73	Device characteristics improvement of a-Inâ€“Gaâ€“Znâ€“O TFTs by low-temperature annealing. Thin Solid Films, 2010, 518, 3017-3021.	1.8	84
74	High Critical Current Density 4 MA/cm²in Co-Doped BaFe₂As₂Epitaxial Films Grown on (La,Sr)(Al,Ta)O₃Substrates without Buffer Layers. Applied Physics Express, 2010, 3, 063101.	2.4	83
75	Intense thermal field electron emission from room-temperature stable electride. Applied Physics Letters, 2005, 87, 254103.	3.3	81
76	Intrinsic excitonic photoluminescence and band-gap engineering of wide-gapp-type oxychalcogenide epitaxial films of LnCuOCh (Ln=La, Pr, and Nd; Ch=S or Se) semiconductor alloys. Journal of Applied Physics, 2003, 94, 5805-5808.	2.5	79
77	Stability and high-frequency operation of amorphous Inâ€“Gaâ€“Znâ€“O thin-film transistors with various passivation layers. Thin Solid Films, 2012, 520, 3778-3782.	1.8	78
78	Electronic Structure of Oxygen Dangling Bond in GlassySiO2: The Role of Hyperconjugation. Physical Review Letters, 2003, 90, 186404.	7.8	76
79	Breast cancer stem cells. Breast Cancer, 2010, 17, 80-85.	2.9	76
80	Electronic Structures and Device Applications of Transparent Oxide Semiconductors: What Is the Real Merit of Oxide Semiconductors?. International Journal of Applied Ceramic Technology, 2005, 2, 285-294.	2.1	72
81	First-principles study of native point defects in crystalline indium gallium zinc oxide. Journal of Applied Physics, 2009, 105, .	2.5	72
82	Electromagnetic properties and electronic structure of the iron-based layered superconductor LaFePO. Physical Review B, 2008, 77, .	3.2	70
83	Water-induced superconductivity inSrFe2As2. Physical Review B, 2009, 80, .	3.2	69
84	Interface and bulk effects for biasâ€”lightâ€illumination instability in amorphousâ€Inâ€”Gaâ€”Znâ€”O thinâ€film transistors. Journal of the Society for Information Display, 2010, 18, 789-795.	2.1	69
85	Photoelectron Spectroscopic Study of C12A7:e-and Alq3Interface:â€‰ The Formation of a Low Electron-Injection Barrier. Journal of Physical Chemistry C, 2007, 111, 8403-8406.	3.1	68
86	Josephson junction in cobalt-doped BaFe2As2 epitaxial thin films on (La,Sr)(Al,Ta)O3 bicrystal substrates. Applied Physics Letters, 2010, 96, .	3.3	68
87	Atomically-flat, chemically-stable, superconducting epitaxial thin film of iron-based superconductor, cobalt-doped. Solid State Communications, 2009, 149, 2121-2124.	1.9	66
88	Effects of postâ€annealing on (110) Cu₂O epitaxial films and origin of low mobility in Cu₂O thinâ€film transistor. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2192-2197.	1.8	65
89	Large Photoresponse in Amorphous Inâ€“Gaâ€“Znâ€“O and Origin of Reversible and Slow Decay. Electrochemical and Solid-State Letters, 2010, 13, H324.	2.2	62
90	Holographic writing of volume-type microgratings in silica glass by a single chirped laser pulse. Applied Physics Letters, 2002, 81, 1137-1139.	3.3	58

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91	Growth mechanism for single-crystalline thin film of InGaO3(ZnO)5 by reactive solid-phase epitaxy. Journal of Applied Physics, 2004, 95, 5532-5539.	2.5	58
92	Optical and Carrier Transport Properties of Cosputtered Znâ€“Inâ€“Snâ€“O Films and Their Applications to TFTs. Journal of the Electrochemical Society, 2008, 155, H390.	2.9	57
93	Amorphous Inâ€“Gaâ€“Zn-O thin-film transistor with coplanar homojunction structure. Thin Solid Films, 2009, 518, 1309-1313.	1.8	57
94	Third-order optical nonlinearity originating from room-temperature exciton in layered compounds LaCuOS and LaCuOSe. Applied Physics Letters, 2004, 84, 879-881.	3.3	56
95	Localized and Delocalized Electrons in Room-Temperature Stable Electride [Ca₂₄Al₂₈O₆₄]⁴⁺(O²⁻)₂₋_x(e⁻)_{2x}: Analysis of Optical Reflectance Spectra. Journal of Physical Chemistry C, 2008, 112, 4753-4760.	3.1	56
96	Simple Analytical Model of On Operation of Amorphous Inâ€“Gaâ€“Znâ€“O Thin-Film Transistors. IEEE Transactions on Electron Devices, 2011, 58, 3463-3471.	3.0	56
97	Mechanism for Heteroepitaxial Growth of Transparent P-Type Semiconductor:â€‰ LaCuOS by Reactive Solid-Phase Epitaxy. Crystal Growth and Design, 2004, 4, 301-307.	3.0	54
98	Calculation of Crystal Structures, Dielectric Constants and Piezoelectric Properties of Wurtzite-Type Crystals Using Ab-Initio Periodic Hartree-Fock Method. Japanese Journal of Applied Physics, 1996, 35, 4421-4426.	1.5	53
99	Functions of Heteromeric Association Between Adenosine and P2Y Receptors. Journal of Molecular Neuroscience, 2005, 26, 233-238.	2.3	53
100	Excitonic blue luminescence from p-LaCuOSeâ•n-InGaZn5O8 light-emitting diode at room temperature. Applied Physics Letters, 2005, 87, 211107.	3.3	53
101	Amorphous Inâ€“Gaâ€“Znâ€“O Dual-Gate TFTs: Currentâ€“Voltage Characteristics and Electrical Stress Instabilities. IEEE Transactions on Electron Devices, 2012, 59, 1928-1935.	3.0	53
102	High electron doping to a wide band gap semiconductor 12CaOâ˜™7Al2O3 thin film. Applied Physics Letters, 2007, 90, 182105.	3.3	52
103	Formation of inorganic electride thin films via site-selective extrusion by energetic inert gas ions. Journal of Applied Physics, 2005, 97, 023510.	2.5	51
104	Intrinsic carrier mobility in amorphous Inâ€“Gaâ€“Znâ€“O thin-film transistors determined by combined field-effect technique. Applied Physics Letters, 2010, 96, 262105.	3.3	51
105	Thin film fabrication of nano-porous 12CaOÂ·7Al2O3 crystal and its conversion into transparent conductive films by light illumination. Thin Solid Films, 2003, 445, 309-312.	1.8	50
106	Opto-electronic properties and light-emitting device application of widegap layered oxychalcogenides: LaCuOCh(Ch= chalcogen) and La2CdO2Se2. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2800-2811.	1.8	50
107	Comprehensive studies on the stabilities of a-In-Ga-Zn-O based thin film transistor by constant current stress. Thin Solid Films, 2010, 518, 3012-3016.	1.8	50
108	Thin Film Growth and Device Fabrication of Iron-Based Superconductors. Journal of the Physical Society of Japan, 2012, 81, 011011.	1.6	50

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109	Roles of Hydrogen in Amorphous Oxide Semiconductor In-Ga-Zn-O: Comparison of Conventional and Ultra-High-Vacuum Sputtering. ECS Journal of Solid State Science and Technology, 2014, 3, Q3085-Q3090.	1.8	50
110	Low Threshold Voltage and Carrier Injection Properties of Inverted Organic Light-Emitting Diodes with [Ca₂₄Al₂₈O₆₄]⁴⁺(4e^{â˜}) Cathode and Cu_{2â˜x}Se Anode. Journal of Physical Chemistry C, 2009, 113, 18379-18384.	3.1	49
111	Antiferromagnetic bipolar semiconductor LaMnPO with ZrCuSiAs-type structure. Journal of Applied Physics, 2009, 105, 093916.	2.5	47
112	Device applications of transparent oxide semiconductors: Excitonic blue LED and transparent flexible TFT. Journal of Electroceramics, 2006, 17, 267-275.	2.0	46
113	Operation Characteristics of Thin-Film Transistors Using Very Thin Amorphous Inâ€“Gaâ€“Znâ€“O Channels. Electrochemical and Solid-State Letters, 2011, 14, H197.	2.2	46
114	Field-Induced Current Modulation in Nanoporous Semiconductor, Electron-Doped 12CaOÂ·7Al2O3. Chemistry of Materials, 2005, 17, 6311-6316.	6.7	45
115	ZnO-Based Semiconductors as Building Blocks for Active Devices. MRS Bulletin, 2008, 33, 1061-1066.	3.5	45
116	Origins of Hole Doping and Relevant Optoelectronic Properties of Wide Gap p-Type Semiconductor, LaCuOSe. Journal of the American Chemical Society, 2010, 132, 15060-15067.	13.7	43
117	High critical-current density with less anisotropy in BaFe2(As,P)2 epitaxial thin films: Effect of intentionally grown c-axis vortex-pinning centers. Applied Physics Letters, 2014, 104, .	3.3	43
118	Photoluminescence from Au ion-implanted nanoporous single-crystal12CaOâ™7Al2O3. Physical Review B, 2006, 73, .	3.2	42
119	Identical effects of indirect and direct electron doping of superconducting BaFe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>As<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math> thin films. Physical Review B, 2013, 87, .	3.2	42
120	Thin film growth by pulsed laser deposition and properties of 122-type iron-based superconductor AE(Fe_{1â˜x}Co_x)₂As₂(AE=alkaline earth). Superconductor Science and Technology, 2012, 25, 084015.	3.5	42
121	Wide gap p-type degenerate semiconductor: Mg-doped LaCuOSe. Thin Solid Films, 2003, 445, 304-308.	1.8	41
122	Heteroepitaxial growth of layered semiconductors, LaZnOPn (Pn=P and As). Thin Solid Films, 2008, 516, 5800-5804.	1.8	40
123	Doping effects in amorphous oxides. Journal of the Ceramic Society of Japan, 2012, 120, 447-457.	1.1	40
124	Superconductivity in noncentrosymmetric ternary equiatomic pnictides LaMP(<mml:math) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	3.2	40
125	Control of carrier concentration and surface flattening of CuGaO2 epitaxial films for a p-channel transparent transistor. Thin Solid Films, 2008, 516, 5790-5794.	1.8	39
126	Heteroepitaxial film growth of layered compounds with the ZrCuSiAs-type and ThCr2Si2-type structures: From Cu-based semiconductors to Fe-based superconductors. Physica C: Superconductivity and Its Applications, 2009, 469, 657-666.	1.2	39

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127	Band alignment of InGaZnO4/Si interface by hard x-ray photoelectron spectroscopy. Journal of Applied Physics, 2012, 112, .	2.5	37
128	Amorphous Snâ€“Gaâ€“Znâ€“O channel thinâ€film transistors. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1920-1924.	1.8	36
129	New functionalities in abundant element oxides: ubiquitous element strategy. Science and Technology of Advanced Materials, 2011, 12, 034303.	6.1	36
130	Effects of low-temperature ozone annealing on operation characteristics of amorphous Inâ€“Gaâ€“Znâ€“O thin-film transistors. Thin Solid Films, 2012, 520, 3787-3790.	1.8	36
131	Mobility- and temperature-dependent device model for amorphous Inâ€“Gaâ€“Znâ€“O thin-film transistors. Thin Solid Films, 2014, 559, 40-43.	1.8	36
132	Synthesis of single-phase layered oxychalcogenide La2CdO2Se2: crystal structure, optical and electrical properties. Journal of Materials Chemistry, 2004, 14, 2946.	6.7	35
133	Microstructure and transport properties of [001]-tilt bicrystal grain boundaries in iron pnictide superconductor, cobalt-doped BaFe2As2. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 515-519.	3.5	35
134	Sn[sub 0.9]In[sub 0.1]P[sub 2]O[sub 7]-Based Organic/Inorganic Composite Membranes. Journal of the Electrochemical Society, 2007, 154, B63.	2.9	34
135	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>LaCo</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="bold">B</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math>: A Co-Based Layered Superconductor with a<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>ThCr</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi>Si</mml:mi><mml:mn> Structure, Physical Review Letters, 2011, 106, 237001.	7.8	34
136	Magnetic Structure and Electromagnetic Properties of LnCrAsO with a ZrCuSiAs-type Structure (Ln =) Tj ETQq0 0 0 rgBT /Overlock 10 Tf	4.6	34
137	Optical Properties and Two-Dimensional Electronic Structure in Wide-Gap Layered Oxychalcogenide:â€‰La2CdO2Se2. Journal of Physical Chemistry B, 2004, 108, 17344-17351.	2.6	33
138	Epitaxial film growth and optoelectrical properties of layered semiconductors, LaMnXO (X=P, As, and) Tj ETQq0 0 0 rgBT /Overlock 10 Tf	2.5	33
139	Narrow Bandgap in Î²-BaZn₂As₂ and Its Chemical Origins. Journal of the American Chemical Society, 2014, 136, 14959-14965.	13.7	33
140	Growth of high-quality SnS epitaxial films by H2S flow pulsed laser deposition. Applied Physics Letters, 2014, 104, .	3.3	32
141	Fabrication of heteroepitaxial thin films of layered oxychalcogenides LnCuOCh (Ln = Laâ€“Nd; Ch =) Tj ETQq1 1 0.784314 rgBT /Overl	2.6	31
142	Solid State Syntheses of 12SrOÂ·7Al₂O₃and Formation of High Density Oxygen Radical Anions, O^{â^'}and O₂^{â^'}. Chemistry of Materials, 2008, 20, 5987-5996.	6.7	30
143	Thin film and bulk fabrication of room-temperature-stable electride C12A7:eâ^' utilizing reduced amorphous 12CaOÂ·7Al2O3(C12A7). Journal of Non-Crystalline Solids, 2008, 354, 2772-2776.	3.1	30
144	Electric double-layer transistor using layered iron selenide Mott insulator TlFe1.6Se2. Proceedings of the National Academy of Sciences of the United States of America, 2014, 111, 3979-3983.	7.1	30

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145	Low and small resistance hole-injection barrier for NPB realized by wide-gap p-type degenerate semiconductor, LaCuOSe:Mg. Organic Electronics, 2008, 9, 890-894.	2.6	29
146	Apparent bipolarity and Seebeck sign inversion in a layered semiconductor: LaZnOP. Physical Review B, 2007, 76, .	3.2	28
147	Surface reactivity and oxygen migration in amorphous indium-gallium-zinc oxide films annealed in humid atmosphere. Applied Physics Letters, 2013, 103, 201904.	3.3	28
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